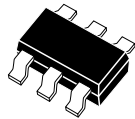


**CMXSH-3  
SUPER-MINI  
TRIPLE ISOLATED  
SURFACE MOUNT  
SCHOTTKY  
SWITCHING DIODE**



**SOT-26 CASE**

# Central™

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXSH-3 type contains three (3) Isolated Schottky Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a super-mini surface mount package, designed for applications requiring low forward voltage drop. Marking code is XH3.

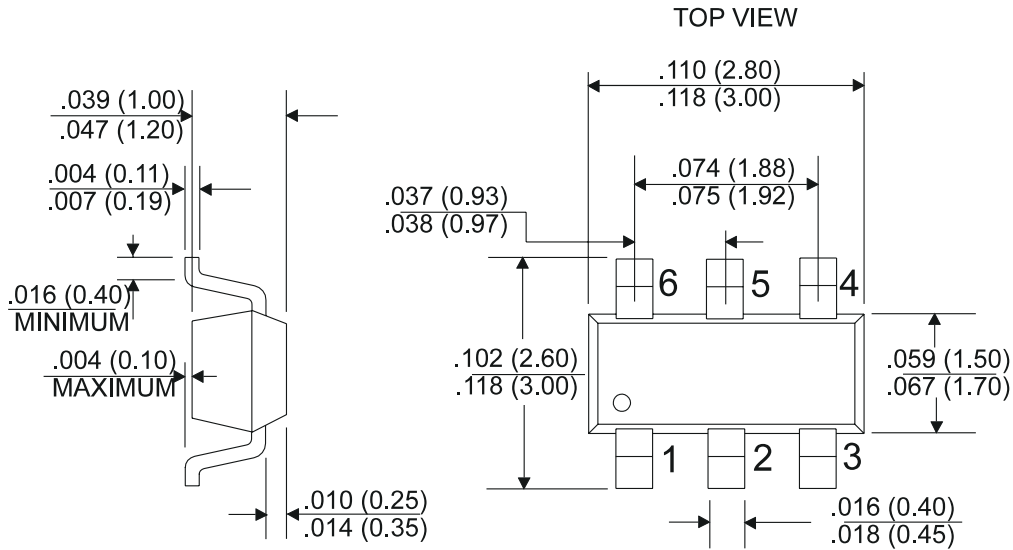
**MAXIMUM RATINGS** ( $T_A=25^\circ\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
Continuous Forward Current	$I_F$	100	mA
Peak Repetitive Forward Current	$I_{FRM}$	350	mA
Forward Surge Current, $t_p=10$ ms	$I_{FSM}$	750	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

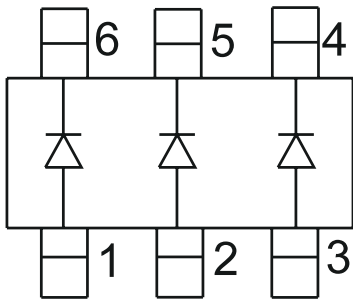
<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$I_R$	$V_R=25\text{V}$		90	500	nA
$I_R$	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	$\mu\text{A}$
$B_{VR}$	$I_R=100\mu\text{A}$	30			V
$V_F$	$I_F=2.0\text{mA}$		0.29	0.33	V
$V_F$	$I_F=15\text{mA}$		0.40	0.45	V
$V_F$	$I_F=100\text{mA}$		0.74	1.00	V
$C_T$	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

**MECHANICAL OUTLINE - SOT-26 CASE**



**All Dimensions in Inches (mm)**

**Pin Configuration**



**Lead Code**

- 1) Anode 1
- 2) Anode 2
- 3) Anode 3
- 4) Cathode 3
- 5) Cathode 2
- 6) Cathode 1